Abstract Submitted
for the MAR17 Meeting of
The American Physical Society

Hyperdoping Si with transition metals for infrared detection[1]
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[1]This work is supported by US Army ARDEC grant no. W15QKN-16-2-0001 and Office of Naval Research grant no. N00014-16-1-2864.

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Date submitted: 16 Nov 2016 Electronic form version 1.4